

FAST RECOVERY DIODES

- Junction Size: Square 180 mils
- Wafer Size: 4"
- V_{RRM} Class: 200 to 600 V
- Passivation Process: Glassivated MOAT
- Reference IR Packaged Part: 20ETF Series

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V_{FM} Maximum Forward Voltage	1300 mV	$T_J = 25^\circ\text{C}$, $I_F = 20\text{ A}$
V_{RRM} Reverse Breakdown Voltage Range	200 to 600 V	$T_J = 25^\circ\text{C}$, $I_{RRM} = 100\text{ }\mu\text{A}$ (1)

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 μm)
Chip Dimensions	180 x 180 mils (4.57 x 4.57 mm) - seed drawing
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	260 μm
Maximum Width of Sawing Line	45 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	Seed drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

IR180LM..CS02CB Series

Bulletin I0124J 07/97

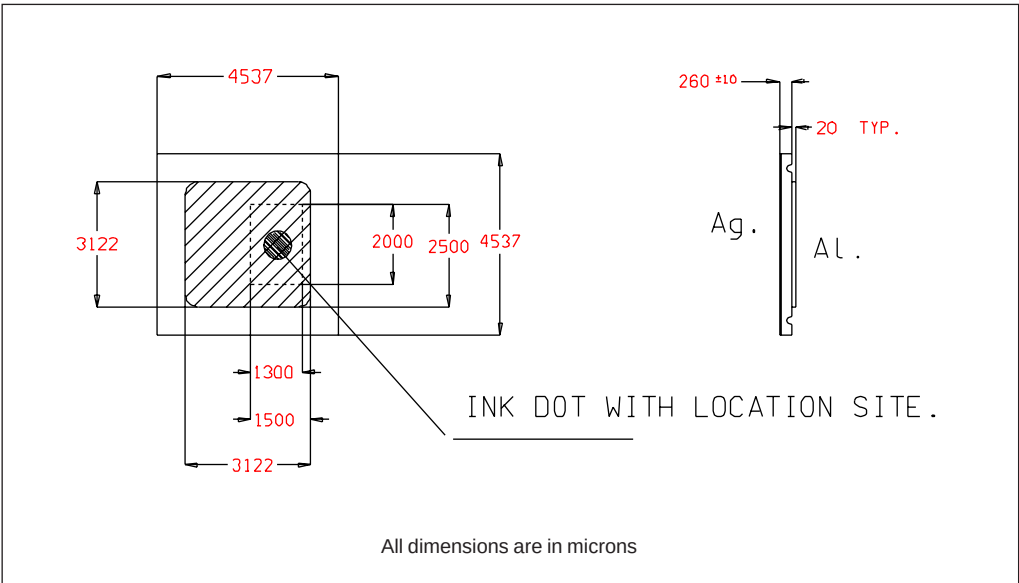
International
IR Rectifier

Ordering Information Table

Device Code							
IR	180	L	M	06	C	S02	CB
1	2	3	4	5	6	7	8
1	- International Rectifier Device						
2	- Chip Dimension in Mils						
3	- Type of Device: L = Wire Bondable Fast Recovery Diode						
4	- Passivation Process: M = Glassivated MOAT						
5	- Voltage code: Code x 100 = V_{RRM}						
6	- Metallization: C = Aluminium (Anode) - Silver (Cathode)						
7	- T_{rr} code: S02 = 200 nsec						
8	- CB = Probed Uncut Die (wafer in box) None = Probed Die in chip carrier						

Available Class
02 = 200 V
04 = 400 V
06 = 600 V

Outline Table



Wafer Layout

